AMORPHOUS AND LIQUID SEMICONDUCTORS

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FOREWORD

The Seventh International Conference on Amorphous and Liquid Semiconductors was held at the University of Edinburgh from 27th June to 1st July, 1977. Most participants and accompanying wives and children (about 350) stayed in the Pollock Halls of Residence; the Conference Sessions were held in the Appleton Tower Building. The main social occasions such as the University Reception, the Conference Dinner and the Conference Excursion were enjoyed by everyone; additional visits and a social programme had also been arranged, for non-scientific visitors.

The Conference Committee, which included Dr. J. Midgley and Mr. W. Campbell of the Centre for Industrial Consultancy and Liaison, was responsible for the scientific programme and the local arrangements. We should like to thank all our colleagues for their help, enthusiasm and co-operation during the last two years. We also wish to express our gratitude for the generous assistance given to the Conference by the following:-

I.U.P.A.P.	The Royal Society, London
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The Committee of the 1976 Williamsburg Conference

This volume contains 151 of the contributed and invited papers read at the Edinburgh Conference. At the present stage of development of our subject, rapid publication of the latest results is extremely important. Because of this and also for economic reasons, the Committee decided to produce the Proceedings from camera-ready manuscripts so that the volume should be ready for dispatch within three months of the Conference. Inevitably, some of the finer points of editing have had to be sacrificed, although every effort has been made in the time available to correct obvious errors and improve the presentation.

The editor would like to express his sincere gratitude to Miss M. Hamilton who, in addition, to her other secretarial duties, dealt efficiently with all the preparatory work, the correspondence with authors and with the final corrections to the manuscripts. Special thanks are also due to Mr. G. Stevenson whose company printed the volume, for many helpful discussions at the planning stage and for his professional advice.

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